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2N/PN2905

PNP
SILICON
TRANSISTORS

2N/PN2905 are PNP silicon planar epitaxial transistors. It is intended for driver stage of power amplifiers and switching applications.

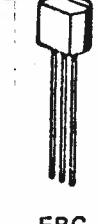
2N2905

T0-39



PN2905

T0-92A



ABSOLUTE MAXIMUM RATINGS

		2N2905	PN2905
Collector-Base Voltage	V _{CBO}	60V	60V
Collector-Emitter Voltage	V _{C EO}	40V	40V
Emitter-Base Voltage	V _{EBO}	5V	5V
Collector Current	I _C	600mA	600mA
Total Power Dissipation @ T _a =25°C	P _{tot}	600mW	500mW
Operating Junction & Storage Temperature T _j , T _{stg}	-65 to +200°C	-55 to +150°C	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CBO}	-60		V	I _C =-10uA I _E =0
Collector-Emitter Breakdown Voltage	LV _{C EO}	-40		V	I _C =-10mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5		V	I _E =-10uA I _C =0
Collector Cutoff Current	I _{CBO}	-20	nA		V _{CB} =-50V I _E =0
Collector Cutoff Current	I _{CBO}	-20	uA		V _{CB} =-50V I _E =0
Collector Cutoff Current	I _{CEx}	-50	nA		T _A =150°C
Base Current	I _B	50	nA		V _{CE} =-30V V _{BE} = 0.5V
D.C. Current Gain	h _{FE}	35			V _{CE} =-30V V _{BE} = 0.5V
D.C. Current Gain	h _{FE}	50			V _{CE} =-10V I _C =-100uA
D.C. Current Gain	h _{FE}	75			V _{CE} =-10V I _C =-1mA
D.C. Current Gain	h _{FE}	100	300		V _{CE} =-10V I _C =-10mA
D.C. Current Gain	h _{FE}	30			V _{CE} =-10V I _C =-150mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-0.4		V	V _{CE} =-10V I _C =-500mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-1.6		V	I _C =-150mA I _B =-15mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-1.3		V	I _C =-500mA I _B =-50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	-2.6		V	I _C =-150mA I _B =-15mA
Output Capacitance	C _{ob}	8	pF		V _{CB} =-10V I _E =0
Input Capacitance	C _{ib}	30	pF		V _{EB} =-2V I _C =0
High Frequency Current Gain	h _{fe}	2			V _{CE} =-20V f=100MHz I _C =-50mA

----- CONTINUE -----

ELECTRICAL CHARACTERISTICS @ $T_A=25^{\circ}\text{C}$ (unless otherwise stated) :

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Delay Time	t_d		10	nsec	$I_C=-150\text{mA}$ $I_{B1}=-15\text{mA}$
Rise Time	t_r		40	nsec	$V_{BE(\text{off})}=0$ $R_L=200\text{ohm}$
Turn On Time	t_{on}		45	nsec	
Storage Time	t_s		80	nsec	$I_C=-150\text{mA}$ $I_{B1}=-13\text{mA}$
Fall Time	t_f		30	nsec	$I_{B2}=17\text{mA}$ $R_L=37\text{ohm}$
Turn Off Time	t_{off}		100	nsec	